

In the Claims:

1. (Currently amended) An optically pumped semiconductor laser device ~~having~~
comprising:

a surface-emitting vertical emission region; [(1)] and

at least one monolithically integrated pump radiation source [(2)] for optically pumping
the vertical emission region [(1)],

wherein the at least one pump radiation source [(2)] is set up and arranged in such a
manner that the pump radiation enters the vertical emission region [(1)] in the form of partial
bundles of rays of radiation with different radiation directions so that the pump radiation and the
fundamental mode of the vertical emission region [(1)] have an overlap which is suitable for
the excitation of this fundamental mode.

2. (Currently amended) The semiconductor laser device as claimed in claim 1,
~~characterized in that~~ wherein the partial bundles of rays of radiation come from different pump
radiation sources [(2)] with different main radiation direction.

3. (Currently amended) The semiconductor laser device as claimed in claim 2,
~~characterized in that~~ wherein the pump radiation sources [(2)] are semiconductor lasers with a
closed resonator which encloses the amplifier region.

4. (Currently amended) The semiconductor device as claimed in claim 2,
~~characterized in that~~ wherein the pump radiation sources [(2)] are edge-emitting semiconductor
lasers.

5. (Currently amended) The semiconductor laser device as claimed in claim 2, wherein each of said ~~one of claims 2 to 4~~, characterized in that the pump radiation sources has ~~(2) in each case have~~ a resonator with at least one curved cavity end facet ~~[[3]]~~.

6. (Currently amended) The semiconductor laser device as claimed in claim 2, wherein each of said ~~one of claims 2 to 4~~, characterized in that the pump radiation sources ~~(2) in each case have~~ has a resonator having at least one cavity end facet arrangement which consists of two straight cavity end facets ~~[[4]]~~ which are arranged at right angles to one another.

7. (Currently amended) The semiconductor laser device as claimed in claim 6, ~~characterized in that~~ wherein the two straight cavity end facets ~~[[4]]~~ are arranged in such a manner that the pump radiation is totally reflected on them in the resonator.

8. (Currently amended) The semiconductor laser device as claimed in claim 2, ~~in one of claims 2 to 4, characterized in that~~ wherein one or more of the pump radiation sources ~~[[2]]~~ have a folded resonator with two cavity end facets and at least one inner cavity facet ~~[[5]]~~.

9. (Currently amended) The semiconductor laser device as claimed in claim 8, ~~characterized in that~~ wherein the at least one inner cavity facet ~~[[5]]~~ is arranged in such a manner that the pump radiation is totally reflected on it in the resonator.

10. (Currently amended) The semiconductor laser device as claimed in claim 8, ~~wherein one of claims 8 or 9, characterized in that~~ the cavity end facets are broken crystal facets and the inner cavity facets ~~[[5]]~~ are etched facets.

11. (Currently amended) The semiconductor laser device as claimed in claim 1, ~~characterized in that~~ wherein the partial bundles of rays of radiation come from a pump radiation source ~~[[2]]~~, the radiation of which is conducted through the vertical emission region ~~[[1]]~~ several times in different directions.

12. (Currently amended) The semiconductor laser device as claimed in claim 11, ~~characterized in that~~ wherein the pump radiation source ~~[[2]]~~ has a resonator with a cavity end facet which consists of an etched facet parabolically curved in the main radiation direction of the vertical emission region ~~[[1]]~~, the vertical emission region ~~[[1]]~~ being arranged in the focal point of the parabolically curved and etched facet.

13. (Currently amended) The semiconductor laser device as claimed in claim 11, ~~characterized in that~~ wherein the pump radiation source ~~[[2]]~~ is a semiconductor ring laser.

14. (Currently amended) The semiconductor laser device as claimed in claim 13, ~~characterized in that~~ wherein the resonator of the semiconductor ring laser has at least three inner cavity facets ~~[[5]]~~.

15. (Currently amended) The semiconductor laser device as claimed in claim 14, ~~characterized in that~~ wherein the at least three inner cavity facets ~~[(5)]~~ are arranged in such a manner that the pump radiation is totally reflected on them in the resonator.

16. (Currently amended) The semiconductor laser device as claimed in claim 1 ~~wherein one of claims 1 to 15, characterized in that~~ the transition from the at least one pump radiation source ~~[(2)]~~ to the vertical emission region ~~[(1)]~~ is curved and is distinguished by a change in the index of refraction so that the pump radiation is focused in the vertical emission region ~~[(1)]~~.

17. (New) The semiconductor laser device as claimed in claim 11, wherein the transition from the at least one pump radiation source to the vertical emission region is curved and is distinguished by a change in the index of refraction so that the pump radiation is focused in the vertical emission region.